TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

## **TC7MZ157FK**

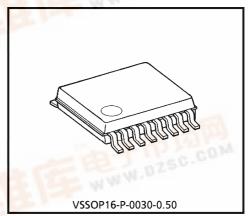
# Low Voltage Quad 2-Channel Multiplexer With 5V Tolerant Inputs And Outputs

The TC7MZ157 is a high performance CMOS MULTIPLEXER. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3V) V<sub>CC</sub> applications, but it could be used to interface to 5V supply environment for inputs.

It consists of four 2-input digital multiplexers with common select and strobe inputs.

When the STROBE input is held "H" level, selection of data is inhibited and all the outputs become "L" level. The SELECT decoding determines whether the A or B inputs get routed to their corresponding Y outputs. All inputs are equipped with protection circuits against static discharge.



Weight: 0.02g (Typ.)

#### **Features**

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Low voltage operation: V<sub>CC</sub> = 2.0~3.6V

• High speed operation :  $t_{pd} = 6.0$ ns (max) ( $V_{CC} = 3.0 \sim 3.6$ V)

• Output current :  $|I_{OH}|/I_{OL} = 24$ mA (min)

 $(V_{CC} = 3.0V)$ 

Latch-up performance : ±500mA

Available in VSSOP (US16)

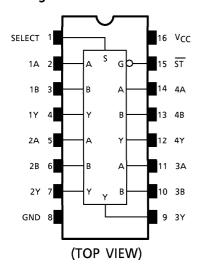
Power down protection is provided on all inputs and outputs.

 Pin and function compatible with the 74 series (74AC/VHC/HC/F/ALS/LS etc.) 157 type.

980910EBA2

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#### Pin Assignment

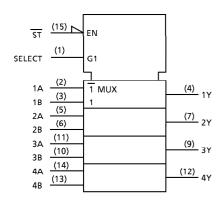


**Truth Table** 

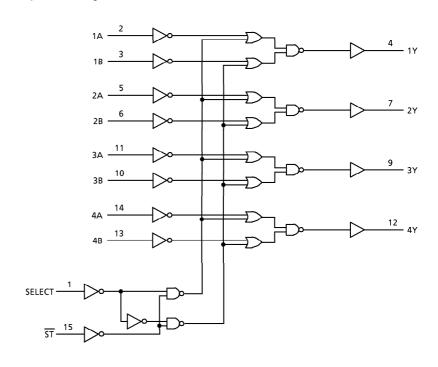
	INP	OUTPUTS		
ST	SELECT	Α	В	Y
Н	Х	Х	Х	L
L	L	L	Х	L
L	L	Н	Х	Н
L	Н	Х	L	L
L	Н	Х	Н	Н

X: Don't Care

#### **IEC Logic Symbol**



#### System Diagram



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#### **Maximum Ratings**

PARAMETER	SYMBOL	RATING	UNIT	
Supply Voltage Range	V <sub>CC</sub> -0.5~7.0		V	
DC Input Voltage	VIN	-0.5~7.0	V	
DC Output Voltage	\/ <b>-</b> <del>-</del>	−0.5~7.0 (Note 1)	<b>V</b>	
DC Output Voltage	Vout	-0.5~V <sub>CC</sub> +0.5 (Note 2)	\ \ \	
Input Diode Current	lικ	<b>– 50</b>	mΑ	
Output Diode Current	lок	±50 (Note 3)	mA	
DC Output Current	lout	± 50	mA	
Power Dissipation	PD	TBD	mW	
DC V <sub>CC</sub> /Ground Current	ICC / IGND	± 100	mA	
Storage Temperature	T <sub>stg</sub>	<b>- 65∼150</b>	°C	

(Note 1):  $V_{CC} = 0V$ 

(Note 2): High or Low State.  $I_{OUT}$  absolute maximum rating must be observed. (Note 3):  $V_{OUT}$  < GND,  $V_{OUT}$  >  $V_{CC}$ 

#### **Recommended Operating Conditions**

PARAMETER	SYMBOL	RATING	UNIT	
Summly Valtage	V	2.0~3.6	\ \	
Supply Voltage	VCC	1.5~3.6 (Note 4)		
Input Voltage	V <sub>IN</sub>	0~5.5	V	
Output Voltage	V	0~5.5 (Note 5)	V	
Output Voltage	VOUT	0~ V <sub>CC</sub> (Note 6)	V	
Output Current	lau /lau	± 24 (Note 7)	mA	
Output Current	IOH/IOL	± 12 (Note 8)		
Operating Temperature	T <sub>opr</sub>	<b>−40~85</b>	°C	
Input Rise And Fall Time	dt/dv	0~10 (Note 9)	ns / V	

(Note 4): Data Retention Only

(Note 5): V<sub>CC</sub> = 0V (Note 6): High or Low State (Note 7):  $V_{CC} = 3.0 \sim 3.6 V$ (Note 8):  $V_{CC} = 2.7 \sim 3.0 V$ (Note 9):  $V_{IN} = 0.8 \sim 2.0 V$ ,  $V_{CC} = 3.0 V$ 

#### **Electrical Characteristics**

DC Characteristics (Ta =  $-40 \sim 85$ °C)

PARAN	ЛЕТЕR	SYMBOL	TEST CONDITION		V <sub>CC</sub> (V)	Min	Max	UNIT
Input	"H" Level	VIH			2.7~3.6	2.0	_	V
Voltage	"L" Level	$V_{IL}$			2.7~3.6	_	0.8	· '
				I <sub>OH</sub> = -100μA	2.7~3.6	V <sub>CC</sub> - 0.2		V
	"H" Level	Voн	VIN = VIH or VIL	$I_{OH} = -12mA$	2.7	2.2		
044				I <sub>OH</sub> = - 18mA	3.0	2.4	_	
Output				$I_{OH} = -24mA$	3.0	2.2	_	
Voltage			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 100μA	2.7~3.6	_	0.2	
	"L" Level	Level V <sub>OL</sub>		I <sub>OL</sub> = 12mA	2.7	_	0.4	
	L Level	VOL		I <sub>OL</sub> = 16mA	3.0	_	0.4	
				I <sub>OL</sub> = 24mA	3.0	_	0.55	
Input Leaka	ge Current	IN	$V_{IN} = 0 \sim 5.5 V$	•	2.7~3.6	_	± 5.0	μΑ
Power Off L Cuurent	eakage	lOFF	V <sub>IN</sub> / V <sub>OUT</sub> = 5.5V		0	_	10.0	$\mu$ A
Quiescent Su	ıpply		V <sub>IN</sub> = V <sub>CC</sub> or GND		2.7~3.6	_	10.0	_
Current	-	lcc	$V_{IN} / V_{OUT} = 3.6 \sim 5.$	5V	2.7~3.6	_	± 10.0	$\mu$ A
Increase In I	CC Per	ΔΙζζ	V <sub>IH</sub> = V <sub>CC</sub> - 0.6V		2.7~3.6	_	500	μΑ

#### AC Characteristics ( $Ta = -40 \sim 85$ °C)

PARAMETER	SYMBOL	TEST CONDITION	V <sub>CC</sub> (V)	Min	Max	UNIT
Propagation Delay	t <sub>pLH</sub>	(Fig. 1, 2)	2.7	_	6.3	nc
Time (A, B-Y)	t <sub>pHL</sub>	(Fig.1, 2)	3.3 ± 0.3	1.5	5.8	ns
Propagation Delay	t <sub>pLH</sub>	(Eig. 1 2)	2.7	_	8.0	nc
Time (SELECT-Y)	t <sub>pHL</sub>	(Fig.1, 2)	3.3 ± 0.3	1.5	7.0	ns
Propagation Delay	t <sub>pLH</sub>	(Eig. 1 2)	2.7	_	8.0	nc
Time (ST-Y)	t <sub>pHL</sub>	(Fig.1, 2)	3.3 ± 0.3	1.5	7.0	ns
Output To Output	tosLH	(Note 10)	2.7	_	_	nc
Skew	tosHL	(Note 10)	3.3 ± 0.3		1.0	ns

(Note 10): Parameter guaranteed by design.  $(t_{OSLH} = |t_{DLHm} - t_{DLHn}|, \ t_{OSHL} = |t_{DHLm} - t_{DHLn}|)$ 

#### **Dynamic Switching Characteristics** (Ta = 25°C, Input $t_r = t_f = 2.5$ ns, $C_L = 50$ pF, $R_L = 500\Omega$ )

PARAMETER	SYMBOL	TEST CONDITION	V <sub>CC</sub> (V)	Тур.	UNIT
Quiet Output Maximum Dynamic V <sub>OL</sub>	V <sub>OLP</sub>	V <sub>IH</sub> = 3.3V, V <sub>IL</sub> = 0V	3.3	0.8	V
Quiet Output Minimum Dynamic V <sub>OL</sub>	V <sub>OL</sub> V	V <sub>IH</sub> = 3.3V, V <sub>IL</sub> = 0V	3.3	8.0	V

#### **Capacitive Characteristics** (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION		V <sub>CC</sub> (V)	Тур.	UNIT
Input Capacitance	C <sub>IN</sub>	_		3.3	7	рF
Output Capacitance	COUT	_		0	8	рF
Power Dissipation Capacitance	C <sub>PD</sub>	f <sub>IN</sub> = 10MHz (Not	te 11)	3.3	25	pF

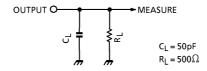
(Note 11): CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

ICC (opr.) = CPD · VCC · fIN + ICC

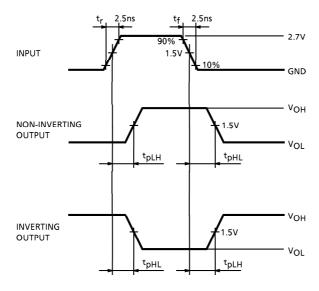
#### **Test Circuit**

Fig.1



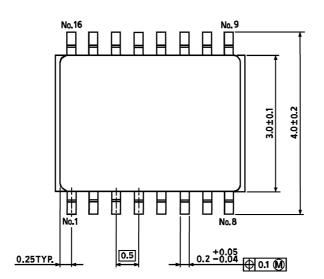
#### **AC Waveform**

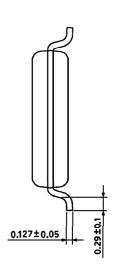
Fig.2 t<sub>pLH</sub>, t<sub>pHL</sub>



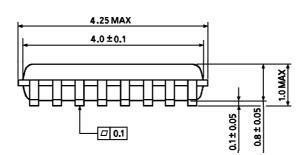
### Outline Drawing

VSSOP16-P-0030-0.50





Unit: mm



Weight: 0.02g (Typ.)